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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	HDMI-CEC, I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	51
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 19x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f071rbt7tr

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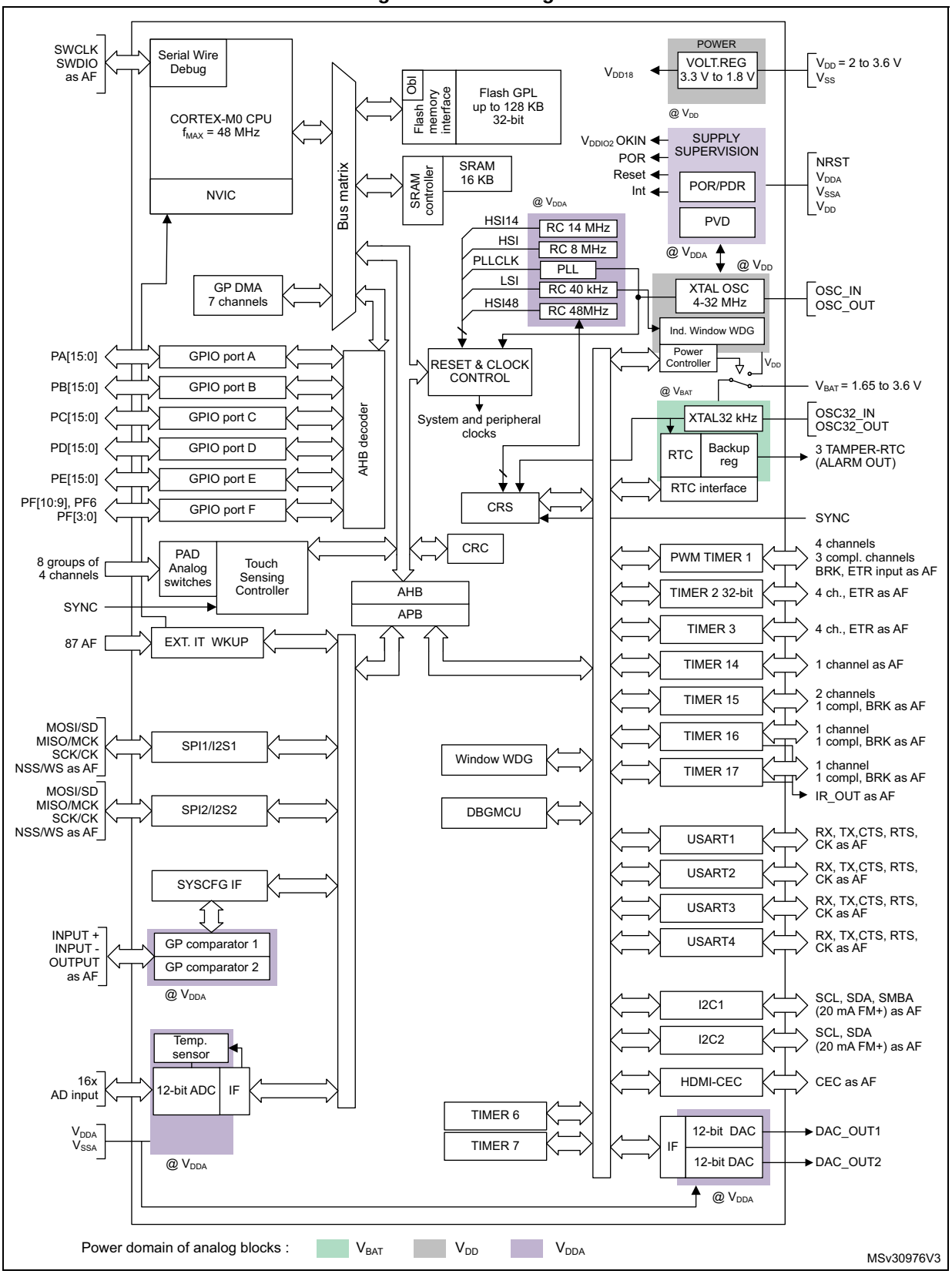


Table 13. STM32F071x8/xB pin definitions (continued)

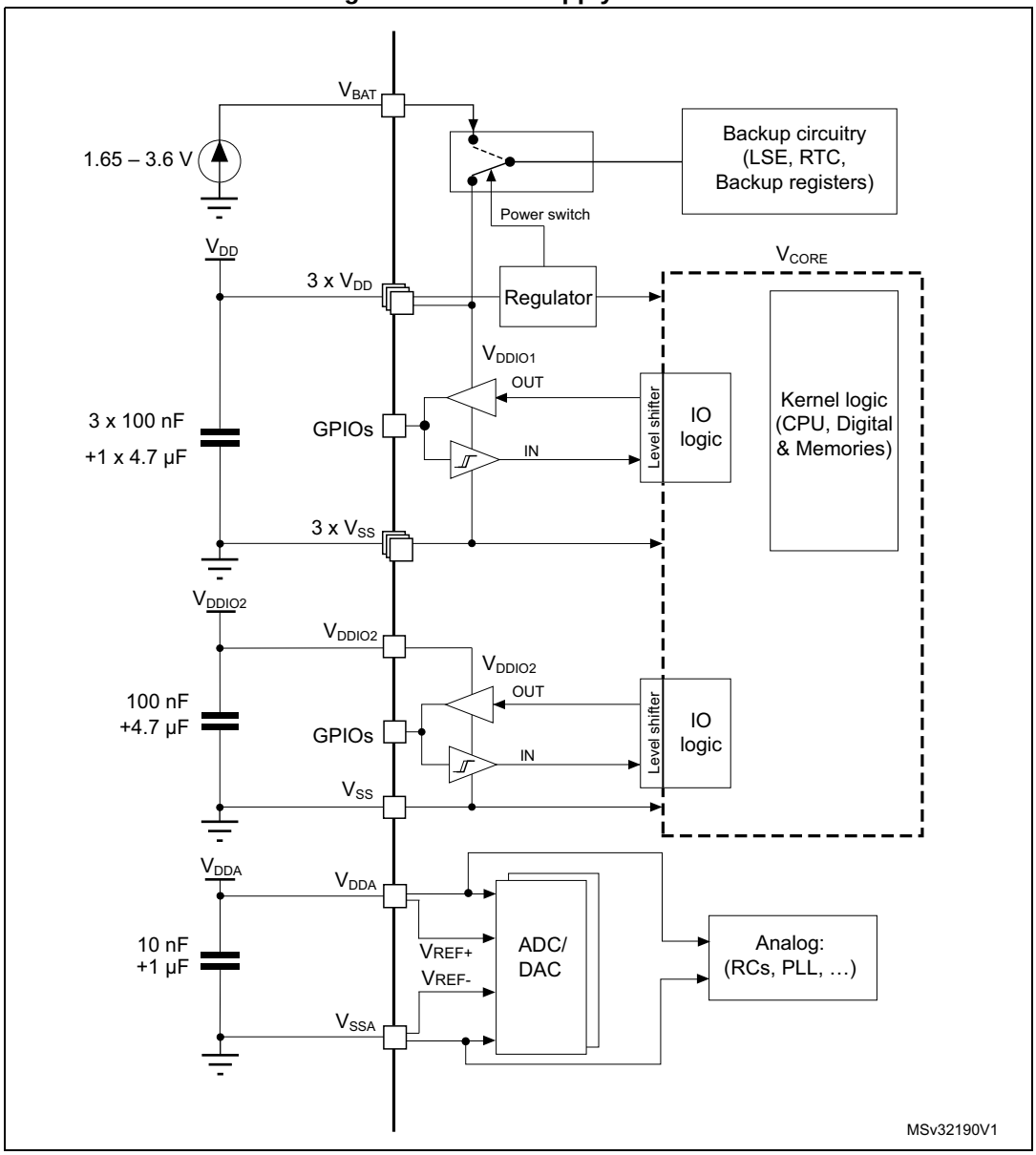
Pin numbers					Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
UFBGA100	LQFP100	LQFP64	LQFP48/UFQFPN48	WLCSP49					Alternate functions	Additional functions
D1	8	3	3	C7	PC14-OSC32_IN (PC14)	I/O	TC	(1) (2)	-	OSC32_IN
E1	9	4	4	C6	PC15-OSC32_OUT (PC15)	I/O	TC	(1) (2)	-	OSC32_OUT
F2	10	-	-	-	PF9	I/O	FT	-	TIM15_CH1	-
G2	11	-	-	-	PF10	I/O	FT	-	TIM15_CH2	-
F1	12	5	5	D7	PF0-OSC_IN (PF0)	I/O	FT	-	CRS_ SYNC	OSC_IN
G1	13	6	6	D6	PF1-OSC_OUT (PF1)	I/O	FT	-	-	OSC_OUT
H2	14	7	7	E7	NRST	I/O	RST	-	Device reset input / internal reset output (active low)	
H1	15	8	-	-	PC0	I/O	TTa	-	EVENTOUT	ADC_IN10
J2	16	9	-	-	PC1	I/O	TTa	-	EVENTOUT	ADC_IN11
J3	17	10	-	-	PC2	I/O	TTa	-	SPI2_MISO, I2S2_MCK, EVENTOUT	ADC_IN12
K2	18	11	-	-	PC3	I/O	TTa	-	SPI2_MOSI, I2S2_SD, EVENTOUT	ADC_IN13
J1	19	-	-	-	PF2	I/O	FT	-	EVENTOUT	WKUP8
K1	20	12	8	E6	VSSA	S	-	-	Analog ground	
M1	21	13	9	F7	VDDA	S	-	-	Analog power supply	
L1	22	-	-	-	PF3	I/O	FT	-	EVENTOUT	
L2	23	14	10	F6	PA0	I/O	TTa	-	USART2_CTS, TIM2_CH1_ETR, TSC_G1_IO1, USART4_TX	RTC_ TAMP2, WKUP1, COMP1_OUT, ADC_IN0, COMP1_INM6
M2	24	15	11	G7	PA1	I/O	TTa	-	USART2_RTS, TIM2_CH2, TIM15_CH1N, TSC_G1_IO2, USART4_RX, EVENTOUT	ADC_IN1, COMP1_INP

Table 13. STM32F071x8/xB pin definitions (continued)

Pin numbers					Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
UFBGA100	LQFP100	LQFP64	LQFP48/UFQFPN48	WLCSP49					Alternate functions	Additional functions
K3	25	16	12	E5	PA2	I/O	TTa	-	USART2_TX, TIM2_CH3, TIM15_CH1, TSC_G1_IO3	ADC_IN2, COMP2_OUT, COMP2_INM6, WKUP4
L3	26	17	13	E4	PA3	I/O	TTa	-	USART2_RX,TIM2_CH4, TIM15_CH2, TSC_G1_IO4	ADC_IN3, COMP2_INP
D3	27	18	-	-	VSS	S	-	-	Ground	
H3	28	19	-	-	VDD	S	-	-	Digital power supply	
M3	29	20	14	G6	PA4	I/O	TTa	-	SPI1_NSS, I2S1_WS, TIM14_CH1, TSC_G2_IO1, USART2_CK	COMP1_INM4, COMP2_INM4, ADC_IN4, DAC_OUT1
K4	30	21	15	F5	PA5	I/O	TTa	-	SPI1_SCK, I2S1_CK, CEC, TIM2_CH1_ETR, TSC_G2_IO2	COMP1_INM5, COMP2_INM5, ADC_IN5, DAC_OUT2
L4	31	22	16	F4	PA6	I/O	TTa	-	SPI1_MISO, I2S1_MCK, TIM3_CH1, TIM1_BKIN, TIM16_CH1, COMP1_OUT, TSC_G2_IO3, EVENTOUT, USART3_CTS	ADC_IN6
M4	32	23	17	F3	PA7	I/O	TTa	-	SPI1_MOSI, I2S1_SD, TIM3_CH2, TIM14_CH1, TIM1_CH1N, TIM17_CH1, COMP2_OUT, TSC_G2_IO4, EVENTOUT	ADC_IN7
K5	33	24	-	-	PC4	I/O	TTa	-	EVENTOUT, USART3_TX	ADC_IN14
L5	34	25	-	-	PC5	I/O	TTa	-	TSC_G3_IO1, USART3_RX	ADC_IN15, WKUP5
M5	35	26	18	G5	PB0	I/O	TTa	-	TIM3_CH3, TIM1_CH2N, TSC_G3_IO2, EVENTOUT, USART3_CK	ADC_IN8
M6	36	27	19	G4	PB1	I/O	TTa	-	TIM3_CH4, USART3_RTS, TIM14_CH1, TIM1_CH3N, TSC_G3_IO3	ADC_IN9
L6	37	28	20	G3	PB2	I/O	FT		TSC_G3_IO4	-

6.1.6 Power supply scheme

Figure 12. Power supply scheme



Caution: Each power supply pair (V_{DD}/V_{SS}, V_{DDA}/V_{SSA} etc.) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

6.1.7 Current consumption measurement

Figure 13. Current consumption measurement scheme

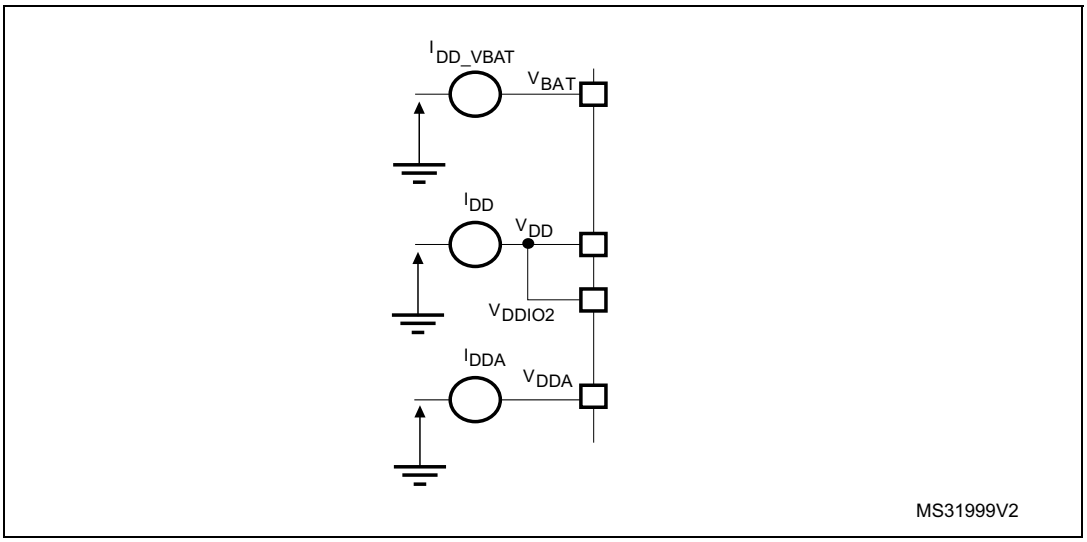


Table 30. Typical and maximum current consumption from the V_{DDA} supply

Symbol	Para-meter	Conditions (1)	f_{HCLK}	V_{DDA} = 2.4 V				V_{DDA} = 3.6 V				Unit
				Typ	Max @ T_A(2)			Typ	Max @ T_A(2)			
					25 °C	85 °C	105 °C		25 °C	85 °C	105 °C	
I_{DDA}	Supply current in Run or Sleep mode, code executing from Flash memory or RAM	HSI48	48 MHz	311	326	334	343	322	337	345	354	µA
		HSE bypass, PLL on	48 MHz	152	170(3)	178	182(3)	165	184(3)	196	200(3)	
			32 MHz	105	121	126	128	113	129	136	138	
			24 MHz	81.9	95.9	99.5	101	88.7	102	107	108	
		HSE bypass, PLL off	8 MHz	2.7	3.8	4.3	4.6	3.6	4.7	5.2	5.5	
			1 MHz	2.7	3.8	4.3	4.6	3.6	4.7	5.2	5.5	
		HSI clock, PLL on	48 MHz	223	244	255	260	245	265	279	284	
			32 MHz	176	195	203	206	193	212	221	224	
			24 MHz	154	171	178	181	168	185	192	195	
		HSI clock, PLL off	8 MHz	74.2	83.4	86.4	87.3	83.4	92.5	95.3	96.6	

1. Current consumption from the V_{DDA} supply is independent of whether the digital peripherals are enabled or disabled, being in Run or Sleep mode or executing from Flash memory or RAM. Furthermore, when the PLL is off, I_{DDA} is independent from the frequency.
2. Data based on characterization results, not tested in production unless otherwise specified.
3. Data based on characterization results and tested in production (using one common test limit for sum of I_{DD} and I_{DDA}).

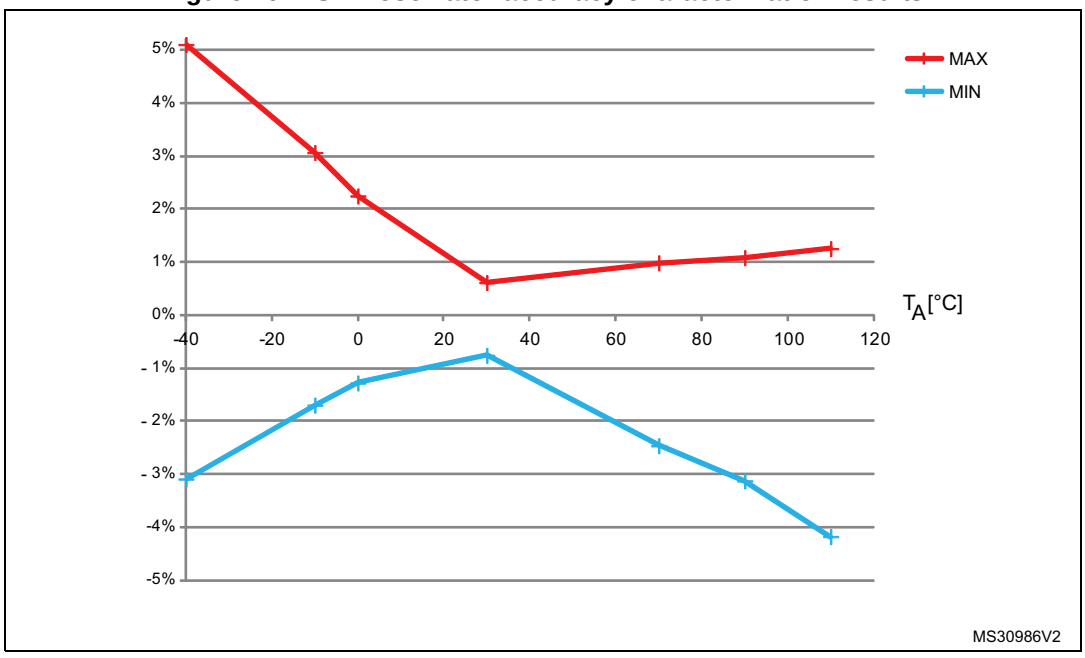
High-speed internal 14 MHz (HSI14) RC oscillator (dedicated to ADC)

Table 42. HSI14 oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI14}	Frequency	-	-	14	-	MHz
TRIM	HSI14 user-trimming step	-	-	-	1(2)	%
$DuCy_{(HSI14)}$	Duty cycle	-	45(2)	-	55(2)	%
ACC_{HSI14}	Accuracy of the HSI14 oscillator (factory calibrated)	T_A = –40 to 105 °C	–4.2(3)	-	5.1(3)	%
		T_A = –10 to 85 °C	–3.2(3)	-	3.1(3)	%
		T_A = 0 to 70 °C	–2.5(3)	-	2.3(3)	%
		T_A = 25 °C	–1	-	1	%
$t_{su(HSI14)}$	HSI14 oscillator startup time	-	1(2)	-	2(2)	µs
$I_{DDA(HSI14)}$	HSI14 oscillator power consumption	-	-	100	150(2)	µA

1. V_{DDA} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design, not tested in production.
3. Data based on characterization results, not tested in production.

Figure 19. HSI14 oscillator accuracy characterization results



Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (for example control registers)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 49. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
				8/48 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 to 30 MHz	-2	dBµV
			30 to 130 MHz	27	
			130 MHz to 1 GHz	17	
			EMI Level	4	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 50. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Packages	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to JESD22-A114	All	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1	WLCSP49	C3	250	V
			All others	C4	500	

1. Data based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 51. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78A	II level A

6.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DDIOx} (for standard, 3.3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of the -5 µA/+0 µA range) or other functional failure (for example reset occurrence or oscillator frequency deviation).

The characterization results are given in *Table 52*.

Negative induced leakage current is caused by negative injection and positive induced leakage current is caused by positive injection.

Figure 21. TC and TTa I/O input characteristics

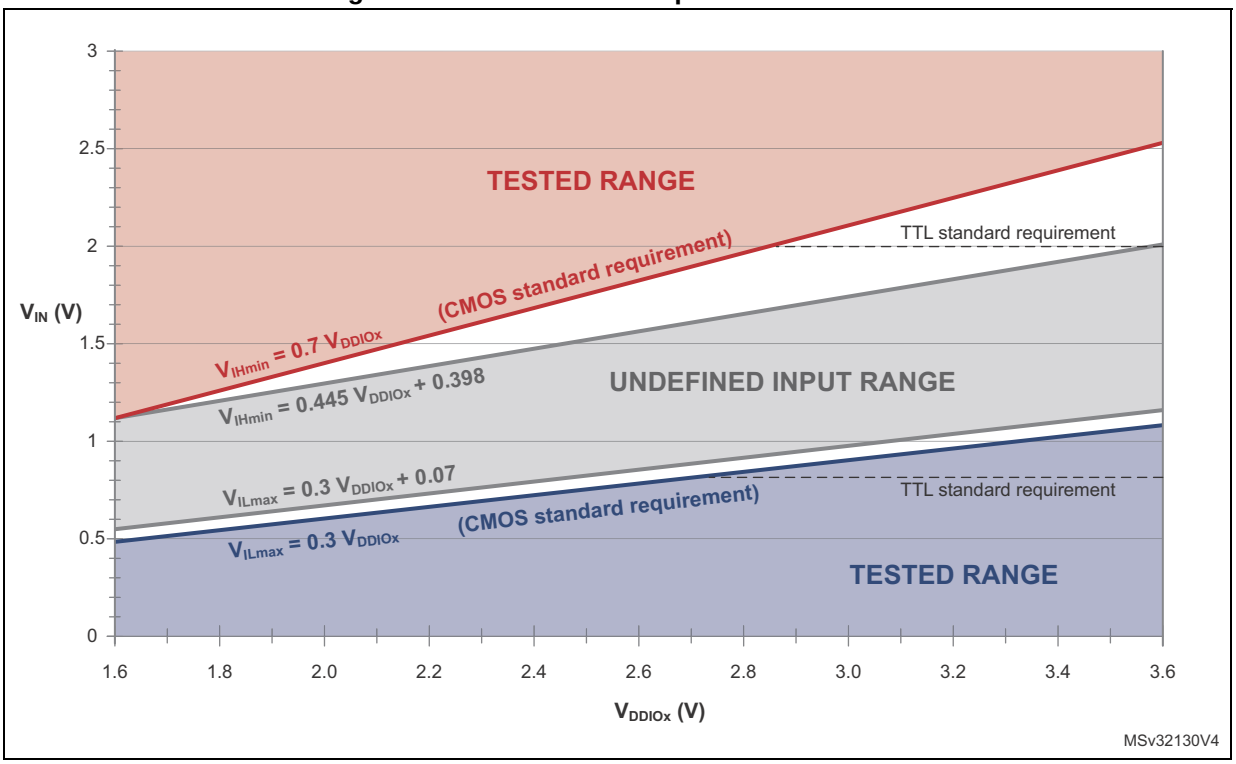


Figure 22. Five volt tolerant (FT and FTf) I/O input characteristics

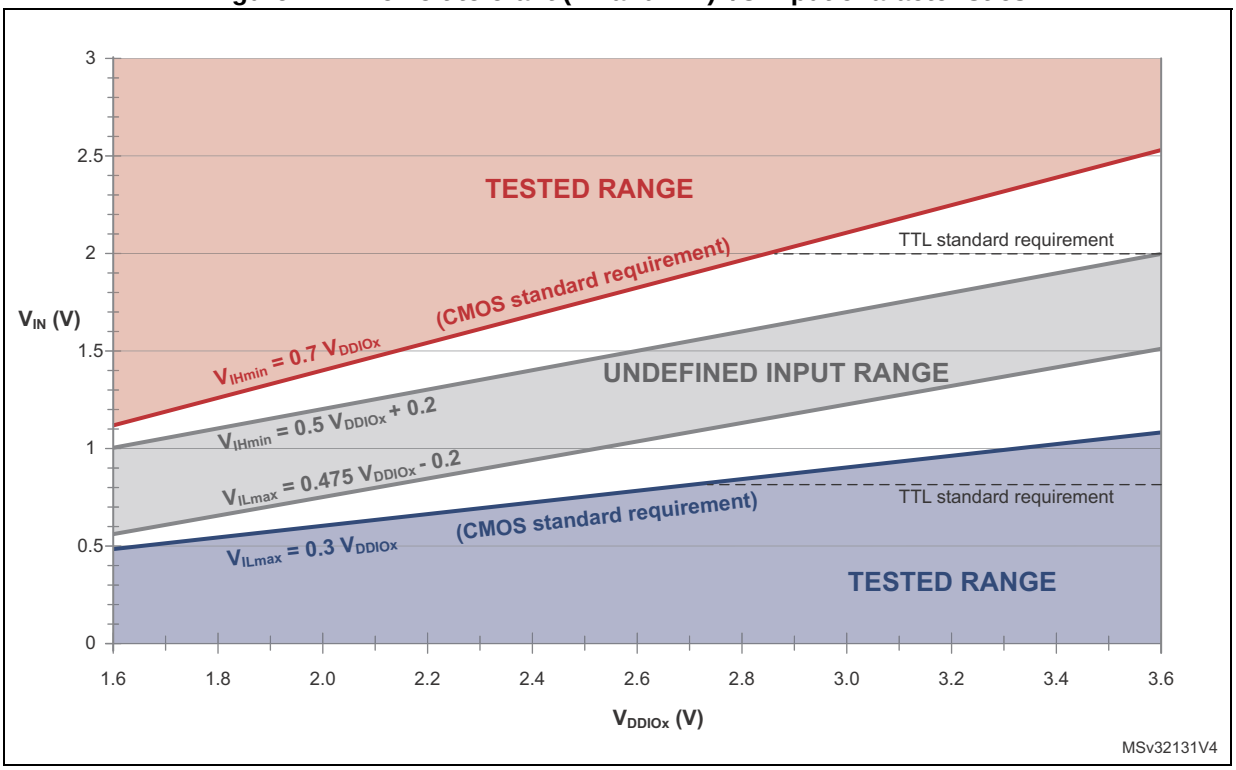
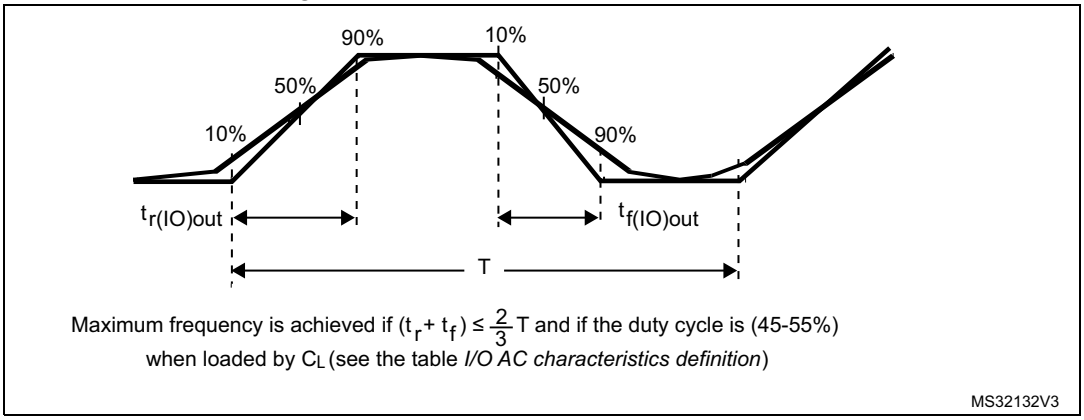


Table 55. I/O AC characteristics(1)(2) (continued)

OSPEEDRy [1:0] value(1)	Symbol	Parameter	Conditions	Min	Max	Unit
Fm+ configuration (4)	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, $V_{DDIOx} \geq 2$ V	-	2	MHz
	$t_{f(IO)out}$	Output fall time		-	12	ns
	$t_{r(IO)out}$	Output rise time		-	34	
	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, $V_{DDIOx} < 2$ V	-	0.5	MHz
	$t_{f(IO)out}$	Output fall time		-	16	ns
	$t_{r(IO)out}$	Output rise time		-	44	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	10	-	ns

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the STM32F0xxxx RM0091 reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design, not tested in production.
3. The maximum frequency is defined in *Figure 23*.
4. When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the STM32F0xxxx reference manual RM0091 for a detailed description of Fm+ I/O configuration.

Figure 23. I/O AC characteristics definition



6.3.15 NRST pin characteristics

The NRST pin input driver uses the CMOS technology. It is connected to a permanent pull-up resistor, R_{PU}.

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

Table 56. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}$	NRST input low level voltage	-	-	-	$0.3\ V_{DD}+0.07$(1)	V
$V_{IH(NRST)}$	NRST input high level voltage	-	$0.445\ V_{DD}+0.398$(1)	-	-	

6.3.17 DAC electrical specifications

Table 60. DAC characteristics

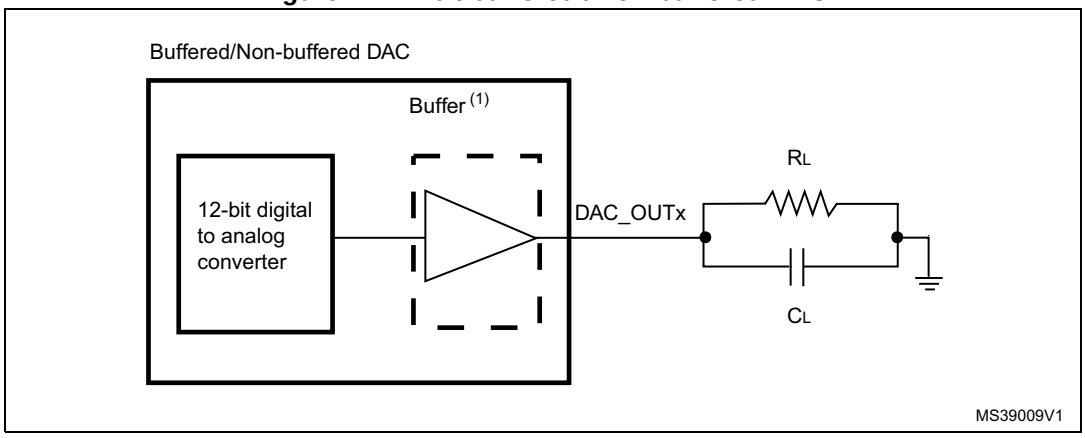
Symbol	Parameter	Min	Typ	Max	Unit	Comments
V_{DDA}	Analog supply voltage for DAC ON	2.4	-	3.6	V	-
R_{LOAD}(1)	Resistive load with buffer ON	5	-	-	kΩ	Load connected to V_{SSA}
		25	-	-	kΩ	Load connected to V_{DDA}
R_O(1)	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and V_{SS} to have a 1% accuracy is 1.5 MΩ
C_{LOAD}(1)	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min(1)	Lower DAC_OUT voltage with buffer ON	0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{DDA} = 3.6 V and (0x155) and (0xEAB) at V_{DDA} = 2.4 V
DAC_OUT max(1)	Higher DAC_OUT voltage with buffer ON	-	-	V_{DDA} – 0.2	V	
DAC_OUT min(1)	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output excursion of the DAC.
DAC_OUT max(1)	Higher DAC_OUT voltage with buffer OFF	-	-	V_{DDA} – 1LSB	V	
I_{DDA}(1)	DAC DC current consumption in quiescent mode(2)	-	-	600	µA	With no load, middle code (0x800) on the input
		-	-	700	µA	With no load, worst code (0xF1C) on the input
DNL(3)	Differential non linearity Difference between two consecutive code-1LSB)	-	-	±0.5	LSB	Given for the DAC in 10-bit configuration
		-	-	±2	LSB	Given for the DAC in 12-bit configuration
INL(3)	Integral non linearity (difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	±1	LSB	Given for the DAC in 10-bit configuration
		-	-	±4	LSB	Given for the DAC in 12-bit configuration
Offset(3)	Offset error (difference between measured value at Code (0x800) and the ideal value = V_{DDA}/2)	-	-	±10	mV	-
		-	-	±3	LSB	Given for the DAC in 10-bit at V_{DDA} = 3.6 V
		-	-	±12	LSB	Given for the DAC in 12-bit at V_{DDA} = 3.6 V

Table 60. DAC characteristics (continued)

Symbol	Parameter	Min	Typ	Max	Unit	Comments
Gain error(3)	Gain error	-	-	±0.5	%	Given for the DAC in 12-bit configuration
$t_{SETTLING}$(3)	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±1LSB	-	3	4	µs	C_{LOAD} ≤ 50 pF, R_{LOAD} ≥ 5 kΩ
Update rate(3)	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	C_{LOAD} ≤ 50 pF, R_{LOAD} ≥ 5 kΩ
t_{WAKEUP}(3)	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	µs	C_{LOAD} ≤ 50 pF, R_{LOAD} ≥ 5 kΩ input code between lowest and highest possible ones.
PSRR+ (1)	Power supply rejection ratio (to V_{DDA}) (static DC measurement	-	–67	–40	dB	No R_{LOAD}, C_{LOAD} = 50 pF

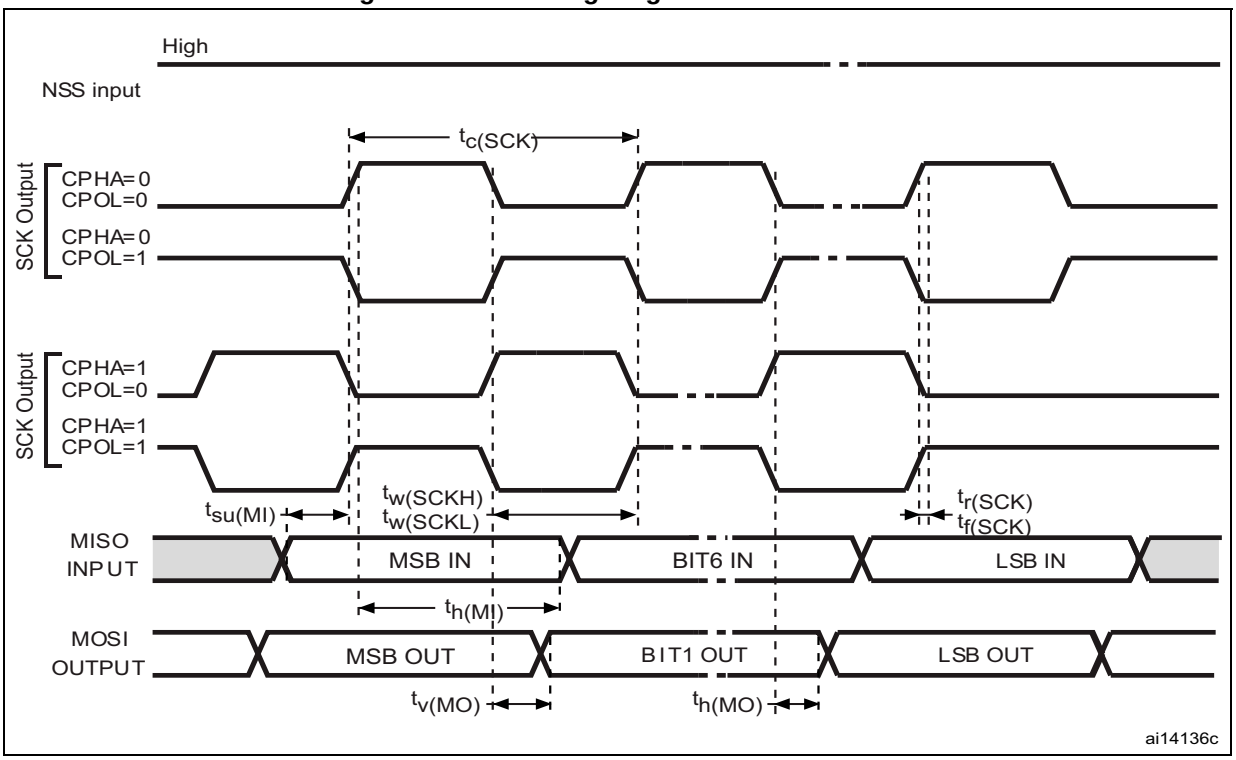
1. Guaranteed by design, not tested in production.
2. The DAC is in “quiescent mode” when it keeps the value steady on the output so no dynamic consumption is involved.
3. Data based on characterization results, not tested in production.

Figure 27. 12-bit buffered / non-buffered DAC



1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

Figure 31. SPI timing diagram - master mode



1. Measurement points are done at CMOS levels: 0.3 V_{DD} and 0.7 V_{DD}.

Table 69. I^2S characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f_{CK} $1/t_{c(CK)}$	I^2S clock frequency	Master mode (data: 16 bits, Audio frequency = 48 kHz)	1.597	1.601	MHz
		Slave mode	0	6.5	
$t_{r(CK)}$	I^2S clock rise time	Capacitive load C_L = 15 pF	-	10	ns
$t_{f(CK)}$	I^2S clock fall time		-	12	
$t_{w(CKH)}$	I^2S clock high time	Master f_{PCLK}= 16 MHz, audio frequency = 48 kHz	306	-	
$t_{w(CKL)}$	I^2S clock low time		312	-	
$t_{v(WS)}$	WS valid time	Master mode	2	-	
$t_{h(WS)}$	WS hold time	Master mode	2	-	
$t_{su(WS)}$	WS setup time	Slave mode	7	-	
$t_{h(WS)}$	WS hold time	Slave mode	0	-	
DuCy(SCK)	I^2S slave input clock duty cycle	Slave mode	25	75	%

Table 70. UFBGA100 package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	6.850	7.000	7.150	0.2697	0.2756	0.2815
D1	-	5.500	-	-	0.2165	-
E	6.850	7.000	7.150	0.2697	0.2756	0.2815
E1	-	5.500	-	-	0.2165	-
e	-	0.500	-	-	0.0197	-
Z	-	0.750	-	-	0.0295	-
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 35. Recommended footprint for UFBGA100 package

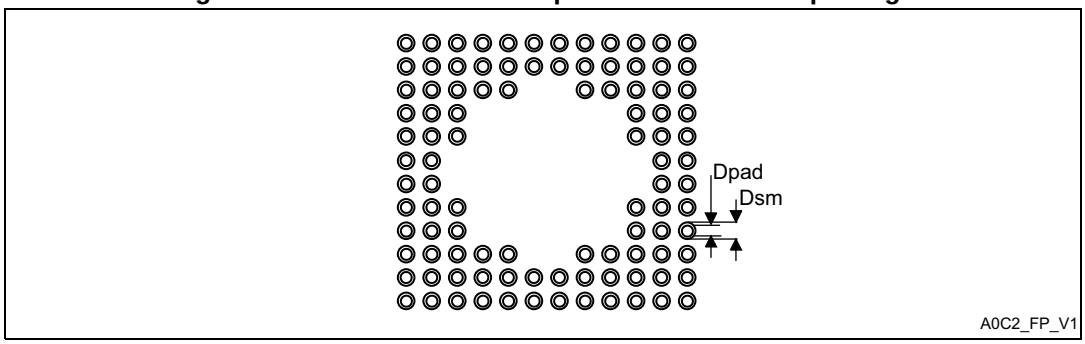


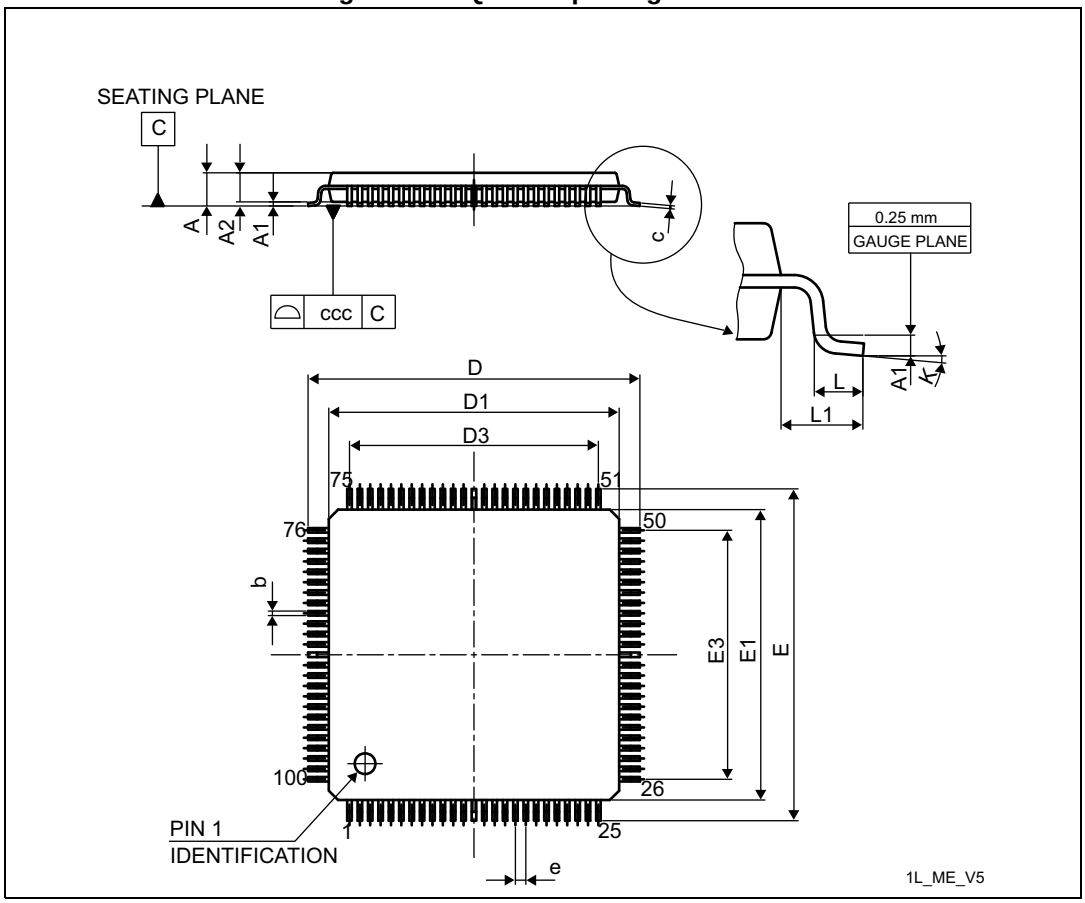
Table 71. UFBGA100 recommended PCB design rules

Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the solder mask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm

7.2 LQFP100 package information

LQFP100 is a100-pin, 14 x 14 mm low-profile quad flat package.

Figure 37. LQFP100 package outline



1. Drawing is not to scale.

Table 72. LQPF100 package mechanical data

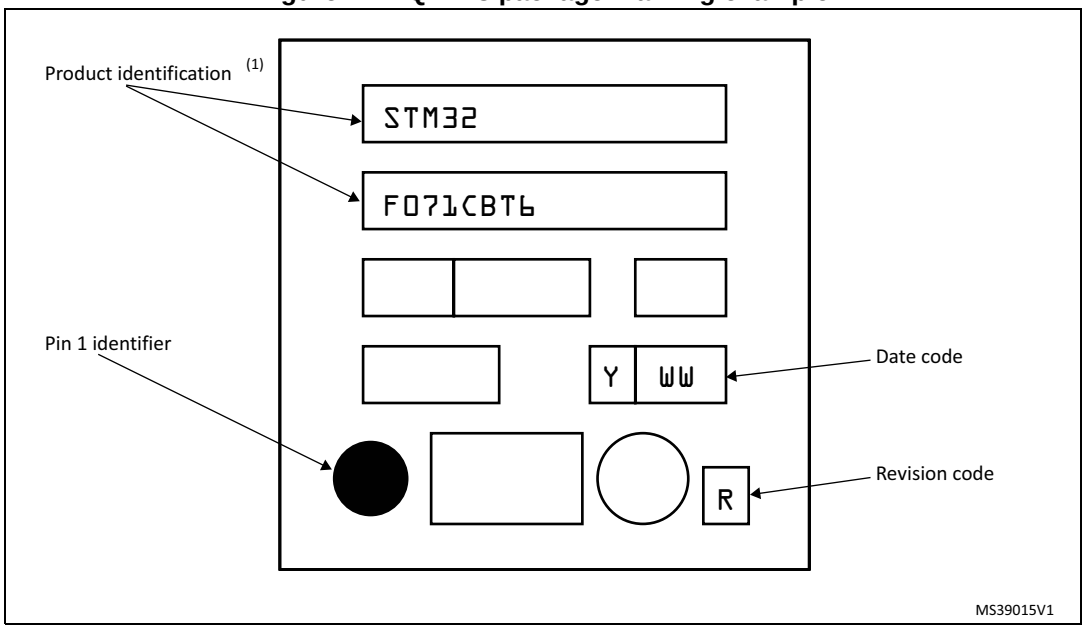
Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 47. LQFP48 package marking example



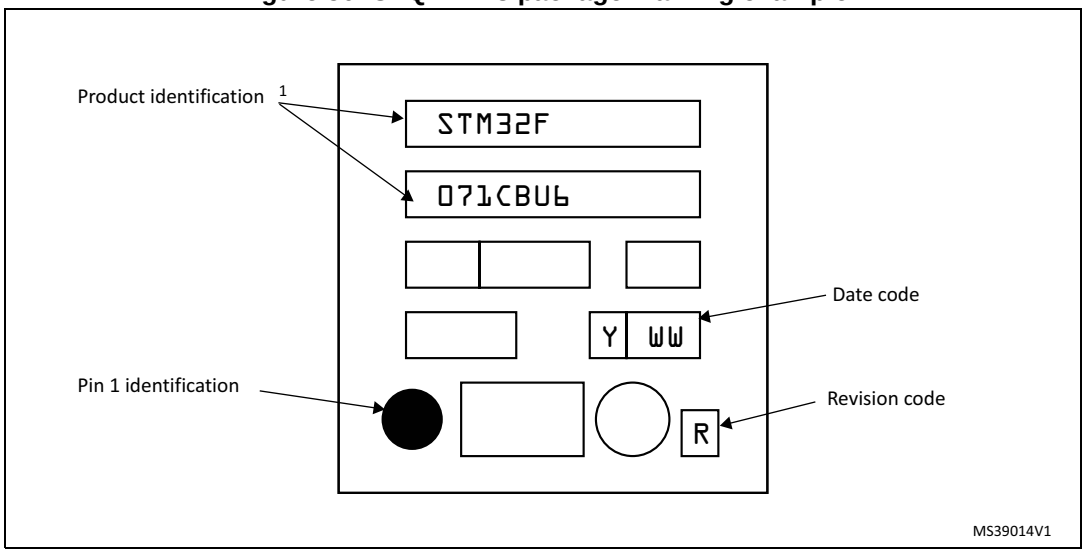
1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 50. UFQFPN48 package marking example



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.